

General Description

The GS 650V 25A power MOSFET is a Low voltage N channel Multi-EPI Super-Junction power MOSFET sample with advanced technology to have better characteristics, such as fast switching time, low Ciss and Crss, low on resistance and excellent avalanche characteristics, making it especially suitable for applications which require superior power density and outstanding efficiency.

Features

- Low gate charge and improved dv/dt capacitance
- 100% avalanche tested
- Fast switching

Mechanical Data

- Case: TO-220, ITO-220, ITO-220-N, TO-263, TO-263-7L, TO-247, TO-3P Packag

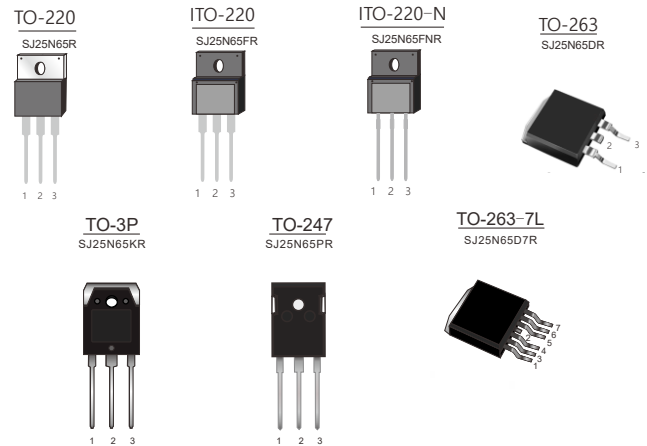
Application

- Switching applications

Ordering Information

Part No.	Package Type	Package	Quality(box)
SJ25N65R	TO-220	Tube	1000
SJ25N65FR	ITO-220	Tube	1000
SJ25N65FNR	ITO-220-N	Tube	1000
SJ25N65DR	TO-263	Tape & Reel	800
SJ25N65PR	TO-247	Tube	360
SJ25N65KR	TO-3P	Tube	360
SJ25N65D7R	TO-263-7	Tape & Reel	800

Product Summary			
V _{DS}	R _{DS(on)} (Ω) Typ	I _D (A)	Q _g (Typ)
650V	0.12 @ 10V 12A	25	110nc



Block Diagram

Pin Definition:
 1. Gate
 2. Drain
 3/4/5/6/7. Source

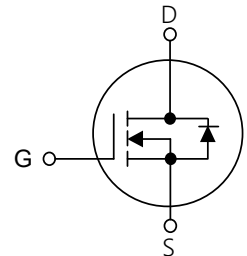


Table1 Absolute Maximum Ratings (T_c=25°C, unless otherwise specified)

Parameter	Symbol	TO-220/TO-263/TO-247/TO-3P / TO-263-7	ITO-220 / ITO-220-N	Unit
Drain-Source Voltage	V _{DS}	650		V
Gate-Source Voltage	V _{GS}	±30		V
Continuous Drain Current	I _D	T _C =25°C	25	25*
		T _C =100°C	15	15*
Pulsed Drain Current (Note 1)	I _{DM}	80		A
Single Pulse Avalanche Energy(Note 2)	E _{AS}	500		mJ
Avalanche Current(Note 1)	I _{AR}	4		A
Repetitive Avalanche Energy(Note 1)	E _{AR}	1.2		mJ
Reverse Diode Recovery dv/dt(Note 3)	dv/dt	15		V/ns
Power Dissipation T _C =25°C	P _D	151	35	W
Operating Junction and Storage Temperature	T _J /T _{STG}	-55 ~ +150		°C

* limited by maximum junction temperature

Table 2. Thermal Characteristics

Parameter	Symbol	TO-220/TO-263 TO-247/TO-3P TO-263-7	ITO-220 ITO-220-N	Unit
Thermal resistance Junction to Ambient	R _{θJA}	62	82	°C/W
Thermal resistance Junction to Case	R _{θJC}	1.0	3.5	°C/W

Table 3. Electrical Characteristics (T_J=25°C, unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	650			V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =650V, V _{GS} =0V			1	μA
Gate- Source Leakage Current	Forward	I _{GSS}			100	nA
	Reverse				-100	nA
On Characteristics(Note 4)						
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250μA	2.0		4.0	V
Static Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =12A		0.12	0.18	Ω
Dynamic Characteristics(Note 5)						
Input Capacitance	C _{ISS}	V _{DS} =25V, V _{GS} =0V, f=1MHz		1650		pF
Output Capacitance	C _{OSS}			90		pF
Reverse Transfer Capacitance	C _{RSS}			9		pF
Switching Characteristics (Note 4)						
Turn-On Delay Time	t _{d(on)}	V _{DD} =520V		28		ns
Turn-On Rise Time	t _R			19		ns
Turn-Off Delay Time	t _{d(off)}			140		ns
Turn-Off Fall Time	t _F	V _{DS} =520V, I _D =12A, V _{GS} =10V		12		ns
Total Gate Charge	Q _G			110		nC
Gate-Source Charge	Q _{GS}			9		nC
Gate-Drain Charge	Q _{GD}		15		nC	
Drain-Source Diode Characteristics and Maximum Ratings						
Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =12A			1.5	V
Maximum Continuous Drain-Source Diode Forward Current	I _S				25	A
Maximum Pulsed Drain-Source Diode Forward Current	I _{SM}				75	A
Reverse Recovery Time	t _{rr}	V _{GS} =0V, I _S =12A		190		ns
Reverse Recovery Charge	Q _{RR}	dI _F /dt=100A/μs (Note 1)		6		μC

Notes : 1 Repetitive Rating: Pulse width limited by maximum junction temperature

2 L=60mH, I_{AS}=3A, V_{DD}=150V, Starting T_J=25°C

3 I_{SD}≤4.5A, di/dt≤200A/μs, V_{DD}≤BV_{DSS}, starting T_J=25°C

4 Pulse Test: Pulse width ≤300μs, Duty cycle≤2%

5 Guaranteed by design, not subject to production

Typical Characteristics Diagrams

Figure 1. Output Characteristics

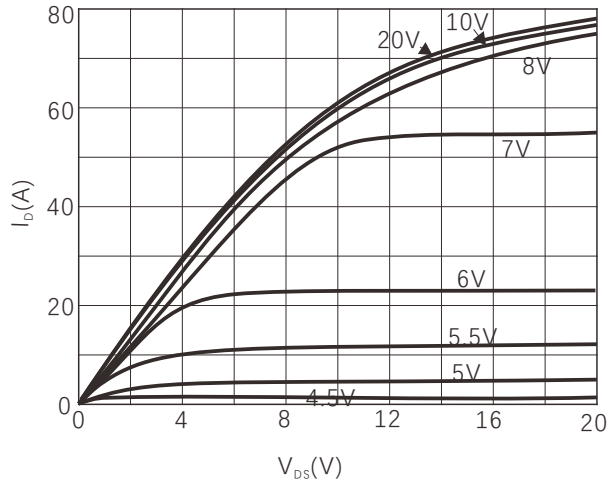


Figure 2. Transfer Characteristics

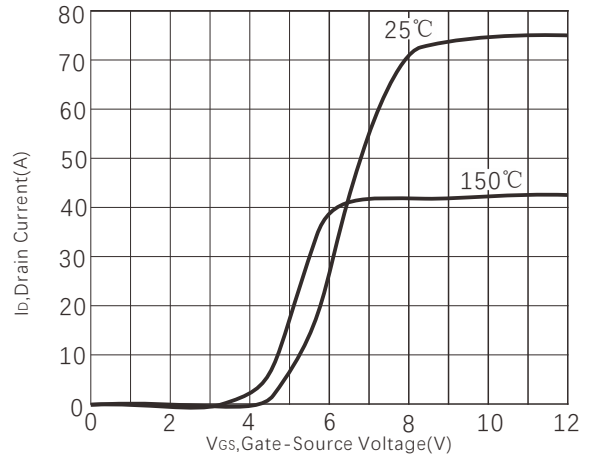


Figure 3. Source-Drain Diode Forward Voltage

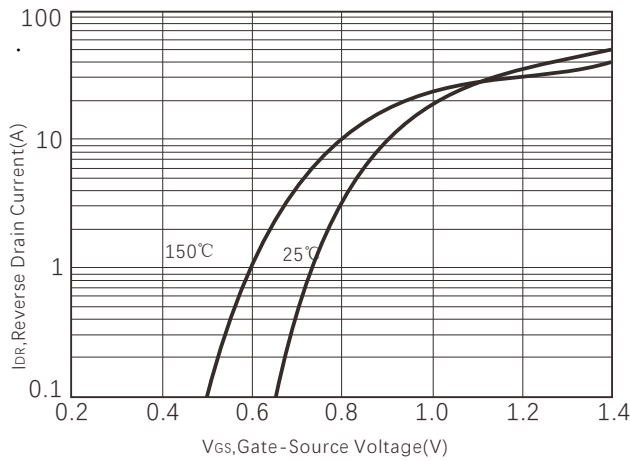


Figure 4. Capacitance

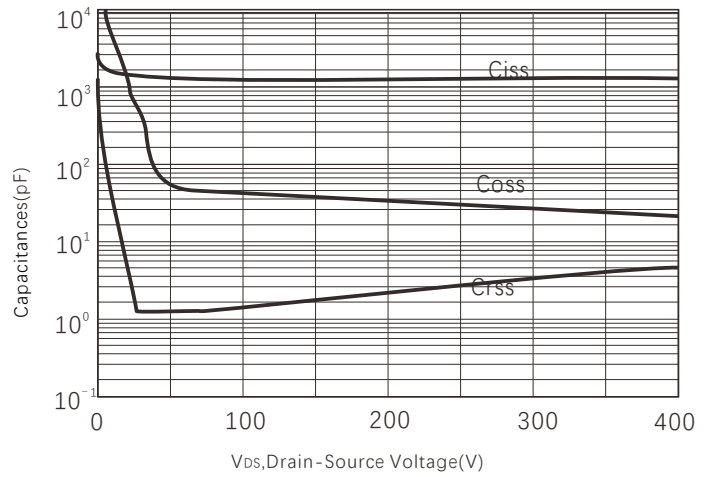


Figure 5. Gate charge

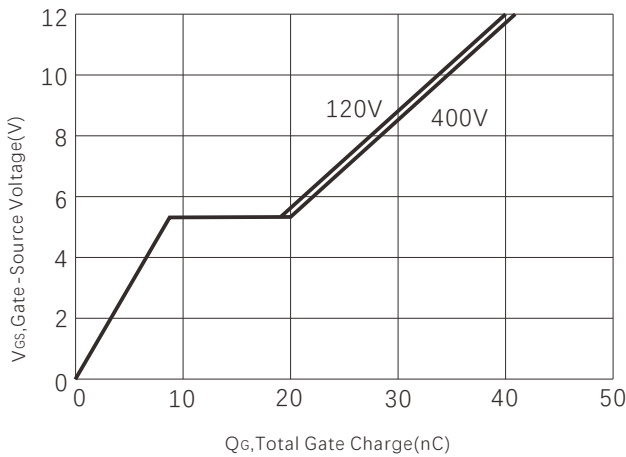


Figure 6. $R_{DS(on)}$ vs Junction Temperature

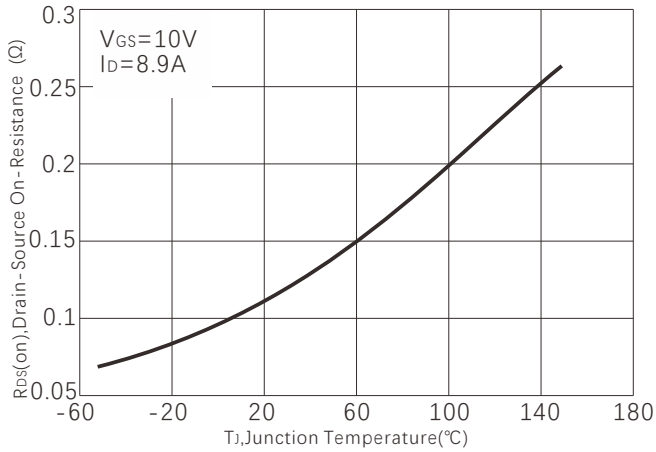


Figure 7. BV_{DSS} vs Junction Temperature

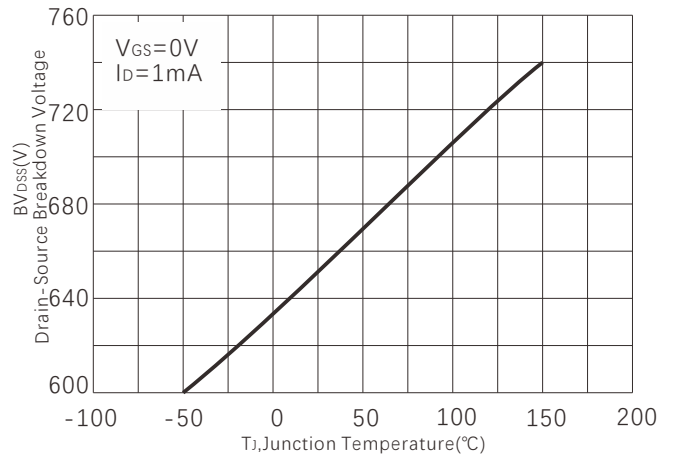


Figure 8. Safe operating area -Non ITO-220

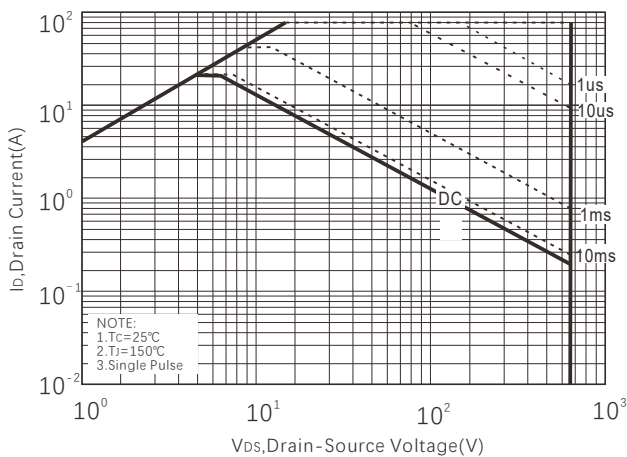


Figure 9. Safe operating area for ITO-220

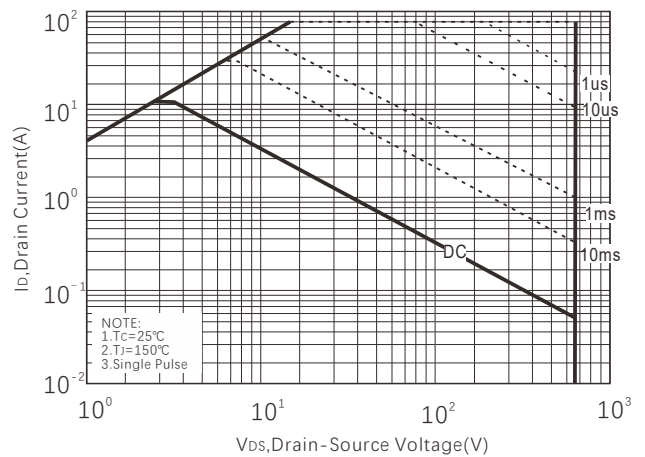


Figure 10. Maximum Transient Thermal Impedance -Non ITO-220

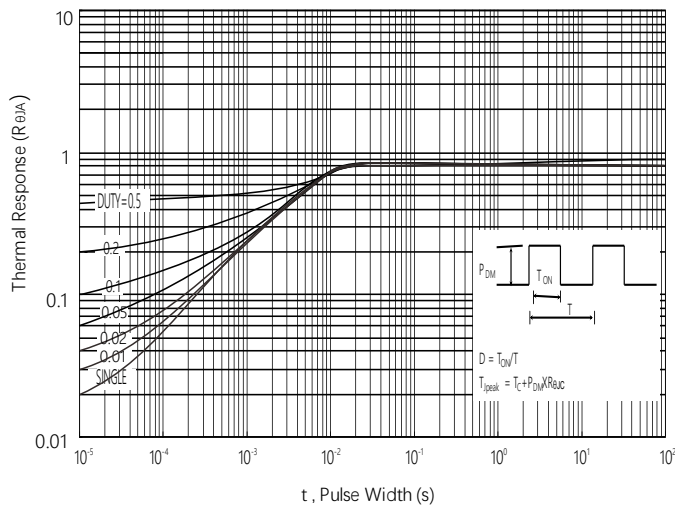


Figure 11. Maximum Transient Thermal Impedance - ITO-220

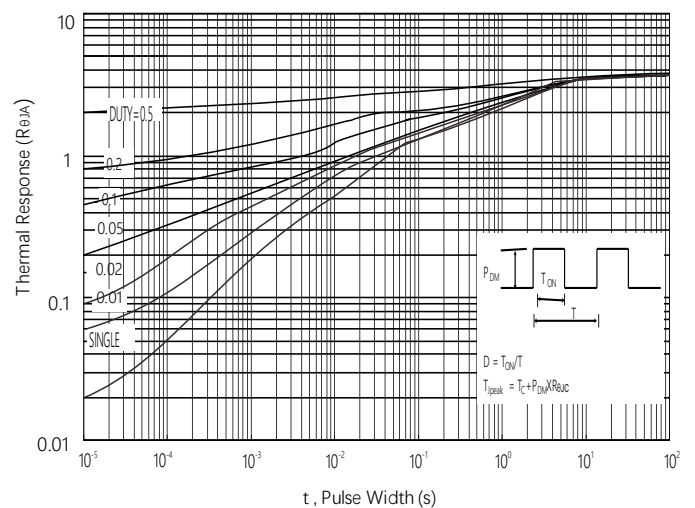


Figure 12. Power dissipation-Non ITO-220

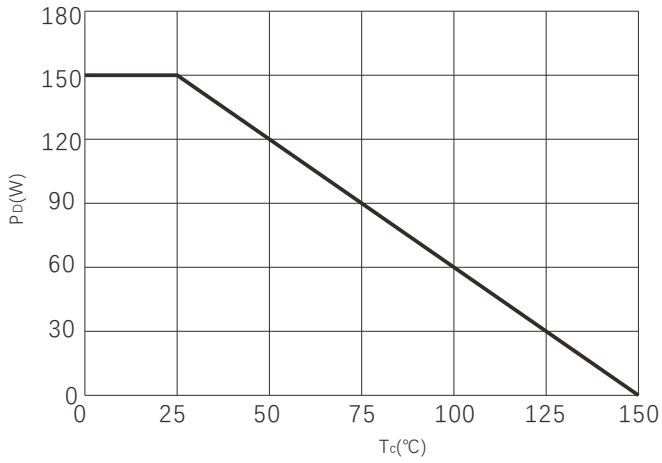
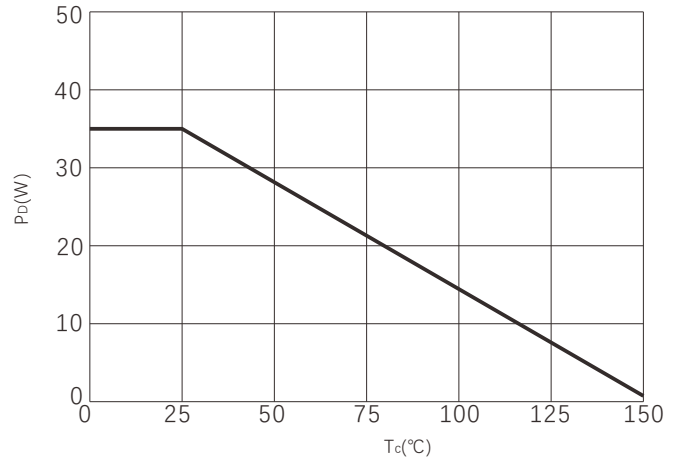
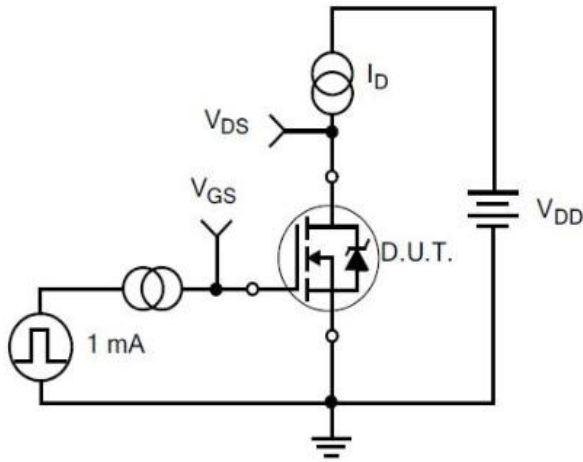


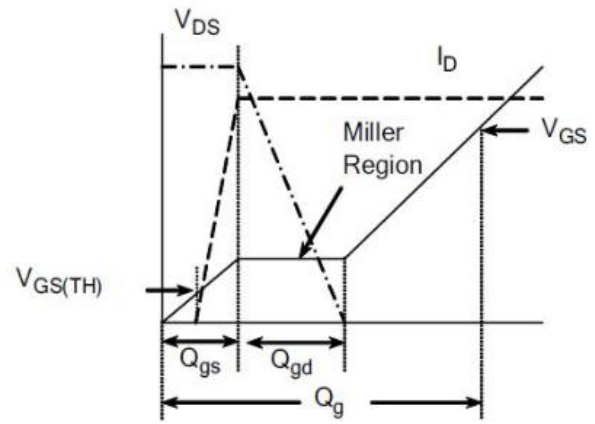
Figure 13. Power dissipation-ITO-220



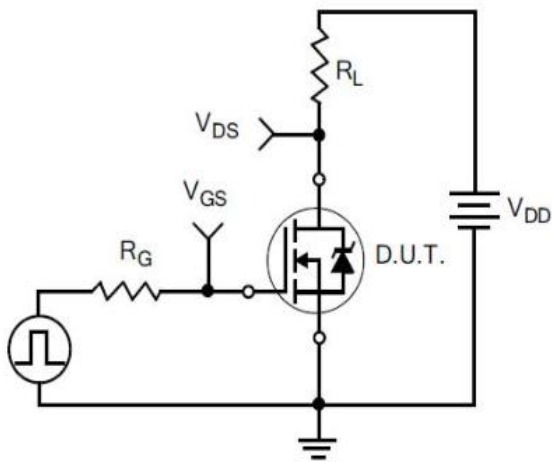
Typical Test Circuit



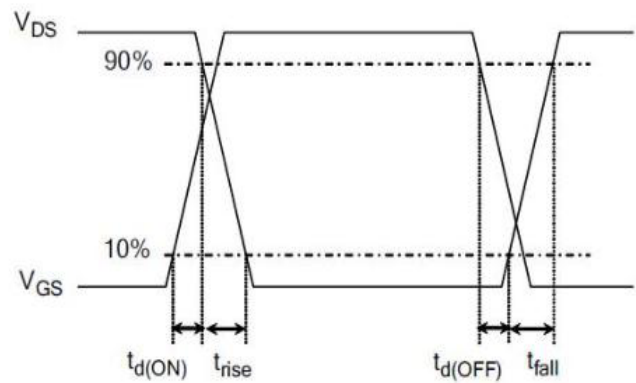
1) Gate Charge Test Circuit



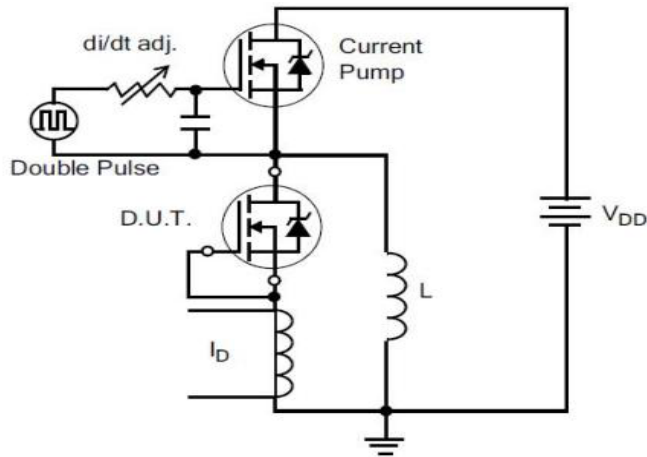
2) Gate Charge Waveform



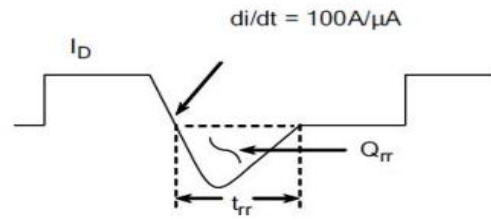
3) Resistive Switching Test Circuit



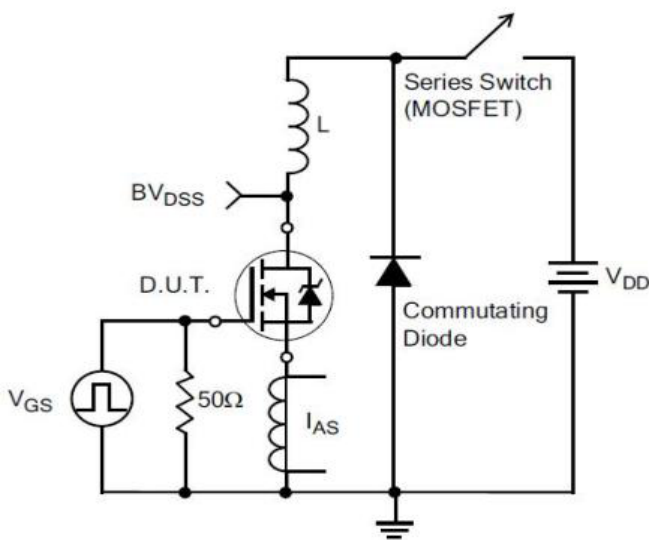
4) Resistive Switching Waveforms



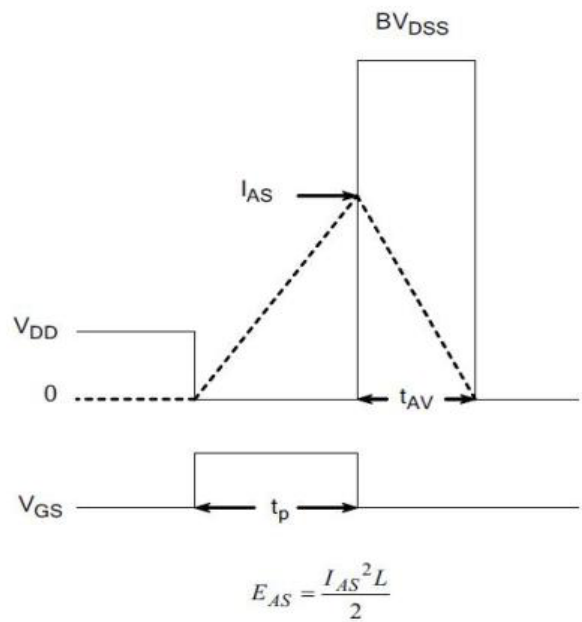
5) Diode Reverse Recovery Test Circuit



6) Diode Reverse Recovery Waveform

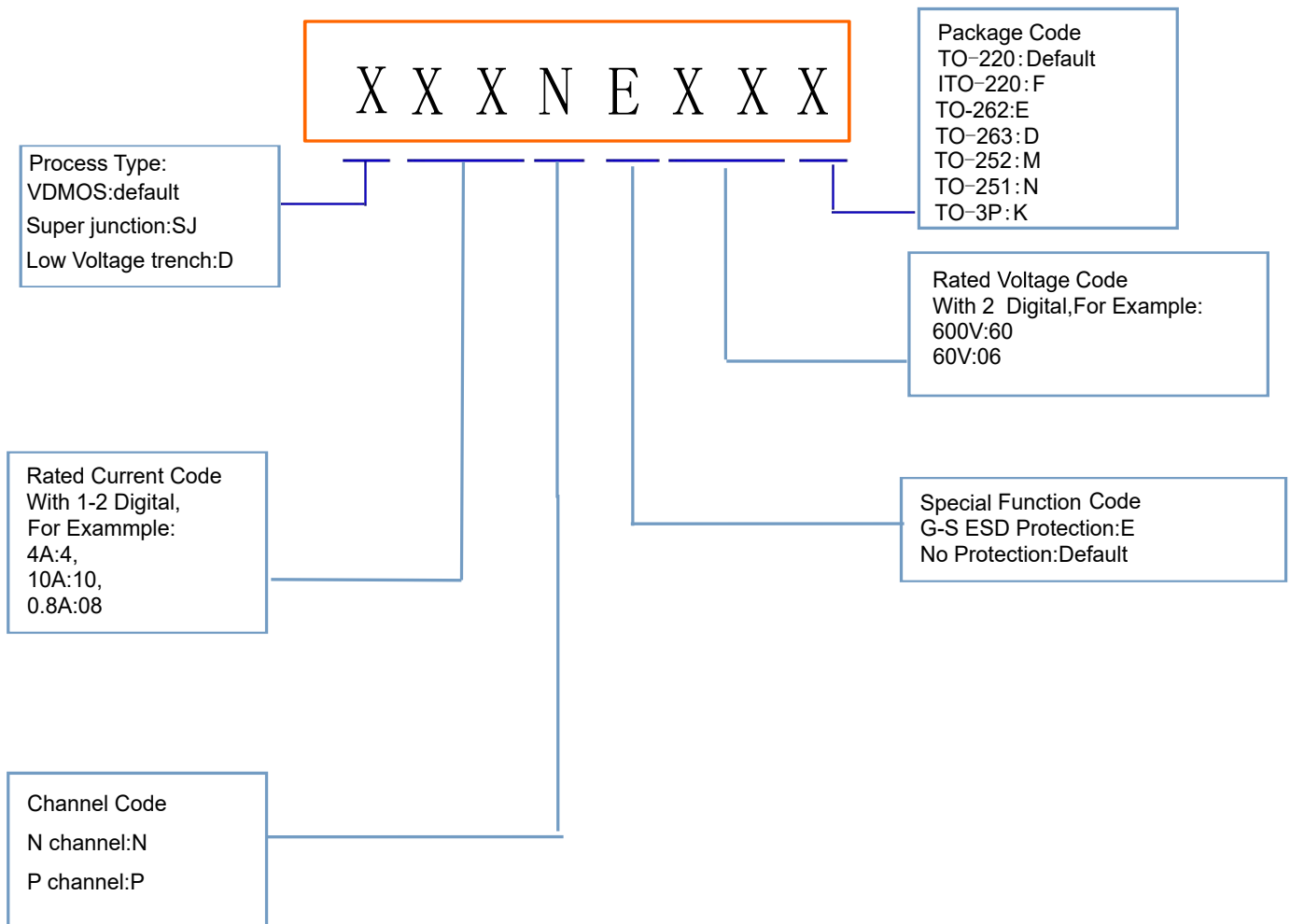


7) . Unclamped Inductive Switching Test Circuit



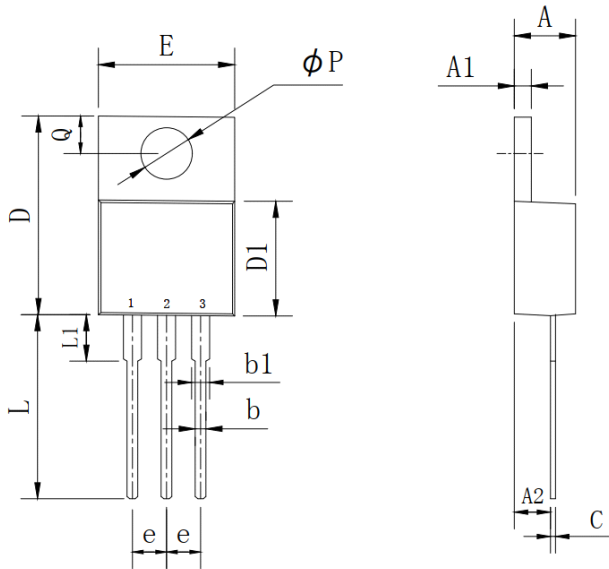
8) Unclamped Inductive Switching Waveforms

Product Names Rules



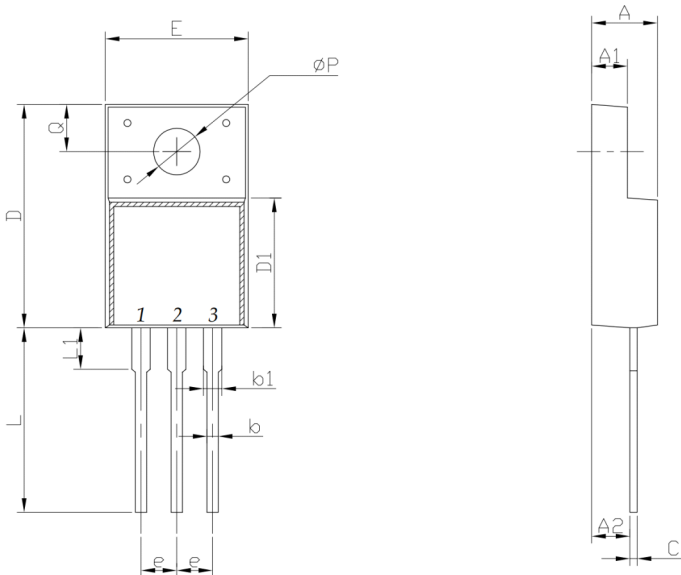
Dimensions

TO-220 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MIN	MAX	MIN	MAX
A	4.25	4.87	0.167	0.192
A1	1.07	1.47	0.042	0.058
A2	2.03	2.92	0.080	0.115
b	0.51	1.11	0.020	0.044
b1	0.97	1.6	0.038	0.063
C	0.3	0.7	0.012	0.028
D	14.6	15.9	0.575	0.626
D1	8.04	9.3	0.317	0.366
E	9.57	10.57	0.377	0.416
e	2.34	2.74	0.092	0.108
L	12.58	14.3	0.495	0.563
L1	2.8	4.2	0.110	0.165
P	3.4	4.14	0.134	0.163
Q	2.45	3	0.096	0.118

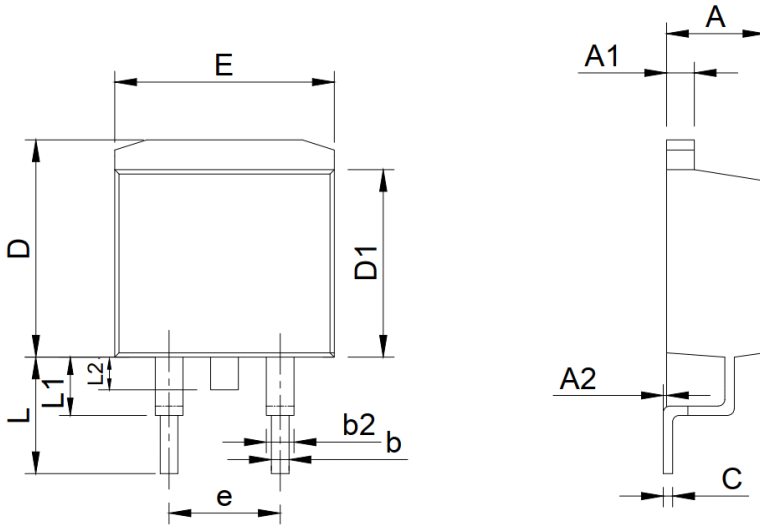
ITO-220 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MIN	MAX	MIN	MAX
A	4.24	4.9	0.167	0.193
A1	2.3	2.92	0.091	0.115
A2	2.61	2.81	0.103	0.111
b	0.3	1	0.012	0.039
b1	0.9	1.55	0.035	0.061
C	0.3	0.7	0.012	0.028
D	14.5	16.36	0.571	0.644
D1	8.8	9.41	0.346	0.370
E	9.5	10.5	0.374	0.413
e	2.3	2.75	0.091	0.108
L	12.6	14	0.496	0.551
L1	2.45	4.3	0.096	0.169
P	2.9	3.8	0.114	0.150
Q	2.5	3.55	0.098	0.140

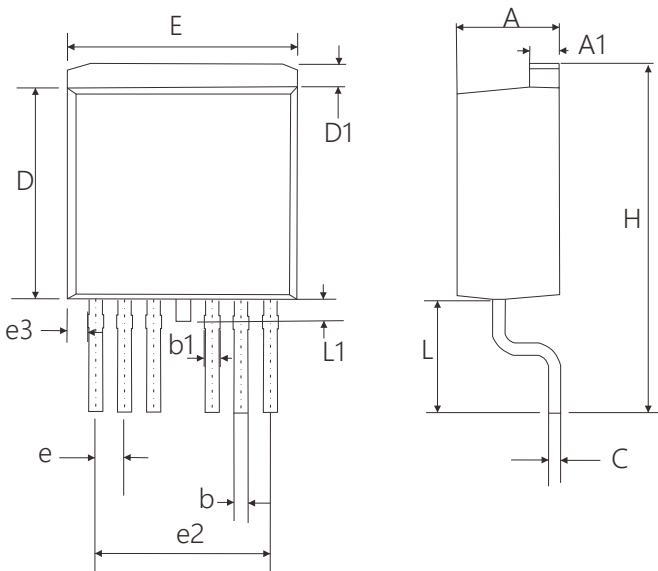
Dimensions

TO-263 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MIN	MAX	MIN	MAX
A	4.25	4.87	0.167	0.192
A1	1.07	1.47	0.042	0.058
A2	0	0.25	0.000	0.010
b	0.61	1.01	0.024	0.040
b1	1.2	1.34	0.047	0.053
C	0.3	0.6	0.012	0.024
D	9.48	10.84	0.373	0.427
D1	8.49	9.3	0.334	0.366
E	9.7	10.31	0.382	0.406
e	4.88	5.28	0.192	0.208
L	4.46	5.85	0.176	0.230
L1	1.33	2.33	0.052	0.092
L2	0	2.2	0.000	0.087

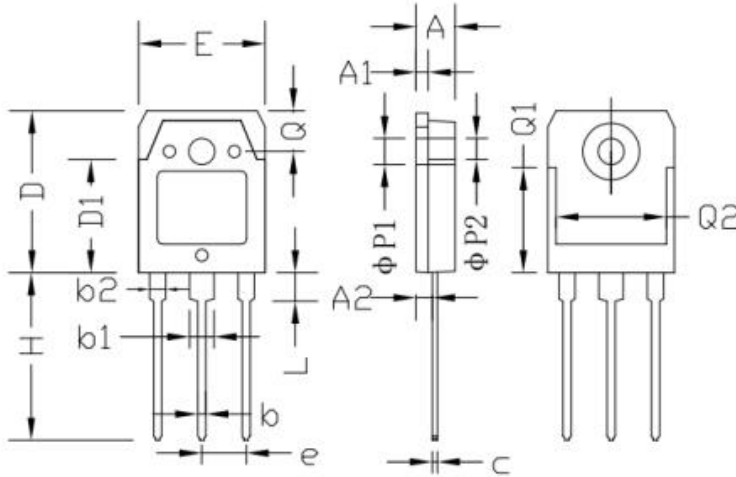
TO-263-7L PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MIN	MAX	MIN	MAX
A	4.25	4.75	0.167	0.187
A1	1.2	1.4	0.047	0.055
b	0.5	0.7	0.020	0.028
b1	0.5	0.9	0.020	0.035
C	0.4	0.6	0.016	0.024
D	9.05	9.45	0.356	0.372
D1	0.7	1.3	0.028	0.051
E	9.8	10.2	0.386	0.402
e	1.07	1.47	0.042	0.058
e2	7.32	7.92	0.288	0.312
e3	0.64	1.04	0.025	0.041
H	14.65	15.65	0.577	0.616
L	4.47	5.47	0.176	0.215
L1	0.90	1.50	0.035	0.059

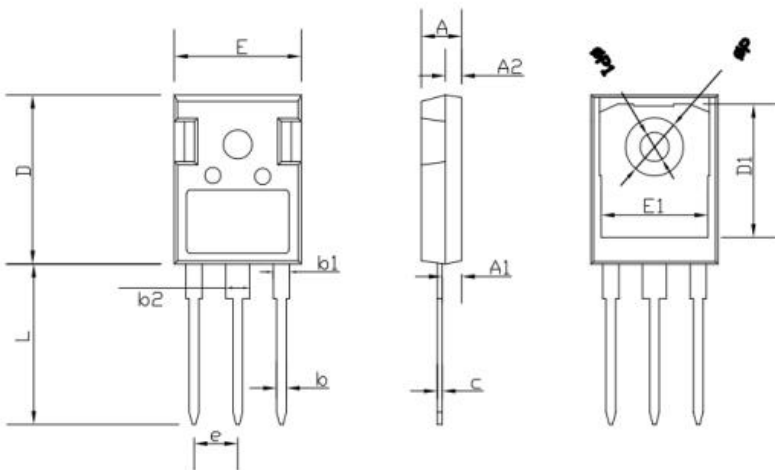
Dimensions

TO-3P PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	min.	max.	min.	max.
A	4.60	5.00	0.181	0.197
A1	1.45	1.65	0.057	0.065
A2	2.20	2.60	0.087	0.102
b	0.80	1.20	0.032	0.047
b1	2.80	3.20	0.110	0.126
b2	1.80	2.20	0.071	0.087
C	0.55	0.75	0.022	0.030
D	19.20	19.70	0.756	0.776
D1	13.10	14.70	0.516	0.578
E	15.40	15.80	0.607	0.623
e	5.45 TYP		0.215 TYP	
H	19.80	20.20	0.780	0.826
L	3.30	3.70	0.130	0.146
ΦP1	3.20 TYP		0.126 TYP	
ΦP2	3.50 TYP		0.138 TYP	
Q	5.00 TYP		0.197 TYP	
Q1	12.40 TYP		0.488 TYP	
Q2	12.6	-	0.496	-

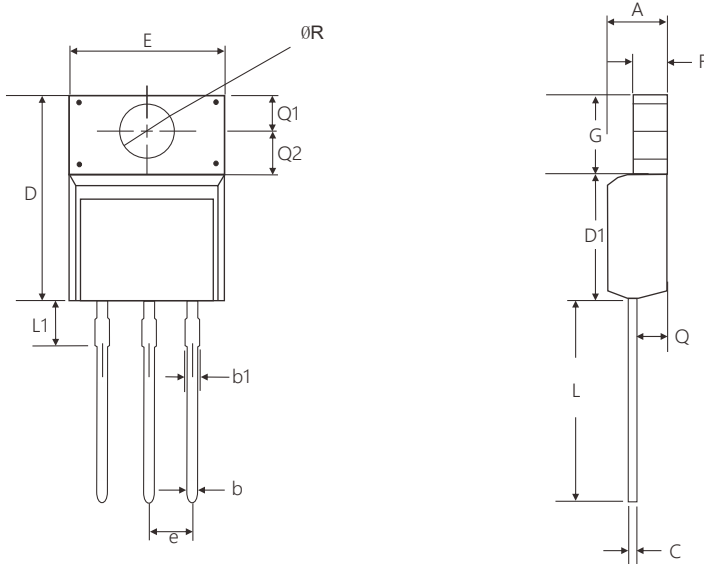
TO-247 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	min.	max.	min.	max.
A	4.90	5.10	0.193	0.201
A1	2.31	2.51	0.091	0.099
A2	1.90	2.10	0.075	0.083
b	1.16	1.26	0.046	0.050
b1	1.96	2.06	0.0772	0.0812
b2	2.96	3.06	0.117	0.121
c	0.59	0.66	0.0232	0.0260
D	20.90	21.10	0.8235	0.8313
D1	16.25	16.85	0.6403	0.6639
E	15.70	15.90	0.6186	0.6265
E1	13.10	13.50	0.5161	0.5319
e	5.44		0.2143	
L	19.80	20.10	0.7801	0.7919
ΦP	3.50	3.70	0.1379	0.1458
ΦP1	0	7.30	0	0.2876

Dimensions

TO-220-N PACKAGE OUTLINE DIMENSIONS



ITO-220AB-N		
Dim	Min	Max
A	4.45	4.85
b	0.55	0.70
b1	0.60	0.80
C	0.45	0.60
D	15.50	16.50
D1	9.00	9.50
e	2.54	
E	9.90	10.50
F	2.34	2.74
G	6.30	6.90
L	12.70	13.30
L1	2.20	2.40
Q	2.70	2.90
Q1	3.40	3.60
Q2	3.20	3.40
$\emptyset R$	3.00	3.40

Dimensions in millimeters

Friendship Reminder

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